Silicon NPN Power Transistors 2SC2460

DESCRIPTION

·With TO-3 package
·Complement to type 2SA1050
·Excellent safe operating area

APPLICATIONS

·For audio and general purpose
power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	140	V
V_{CEO}	Collector-emitter voltage	Open base	140	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		12	A
P_C	Collector power dissipation	T_C=25□	100	W
T_j	Junction temperature		175	□
T_{stg}	Storage temperature		-55~200	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=25mA ;I_B=0	140			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=1mA ;I_E=0	140			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ;I_C=0	5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=8A; I_B=0.8A			2.5	V
V_{BE}	Base-emitter on voltage	I_C=6A ; V_{CE}=5V			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=140V; I_E=0			10	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			10	μA
h_{FE-1}	DC current gain	I_C=1A ; V_{CE}=5V	55		240	
h_{FE-2}	DC current gain	I_C=6A ; V_{CE}=-5V	35			
f_T	Transition frequency	I_C=1A ; V_{CE}=10V		70		MHz

PACKAGE OUTLINE

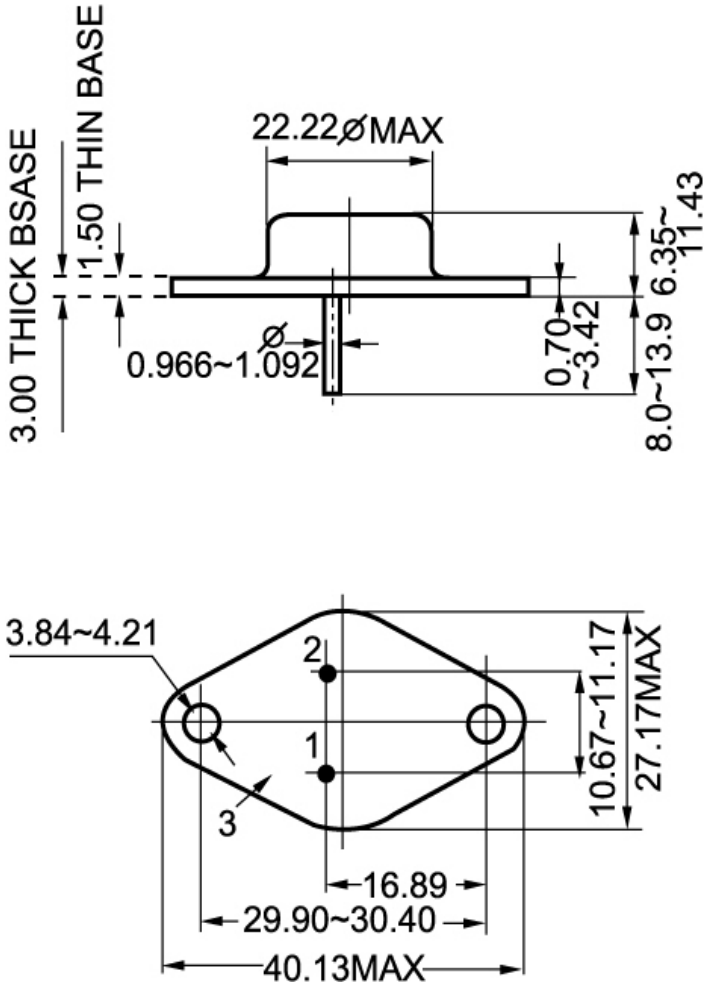

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)